

ABSTRACT OF THE DISCLOSURE

In a photoelectric conversion device with a photoelectric conversion region for accumulating electric charges that correspond to incident light

5 and an amplifying field effect transistor into which a signal charge from the photoelectric conversion region is inputted, the photoelectric conversion region is surrounded by a potential barrier region (a selectively oxidized film and a channel stopper), a

10 nick region (overflow channel) is formed in a part of the potential barrier region, and a drain region of the field effect transistor that has the same conductivity type as the photoelectric conversion region is placed next to the nick region. Thus

15 excess carriers are prevented from flowing into adjacent pixels or other floating regions.